

# Inkjet-Printed Top-Gate Thin-Film Transistors Based on InGaSnO Semiconductor Layer with Improved Etching Resistance

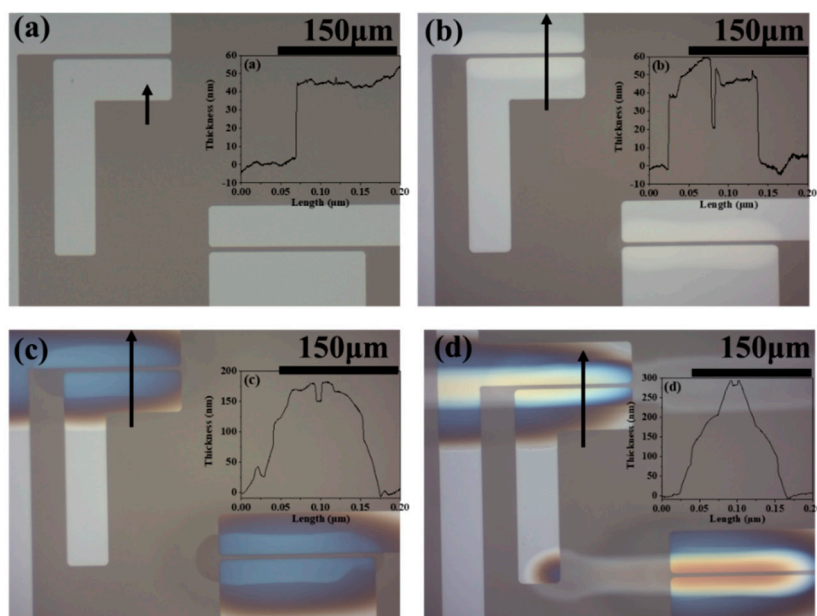
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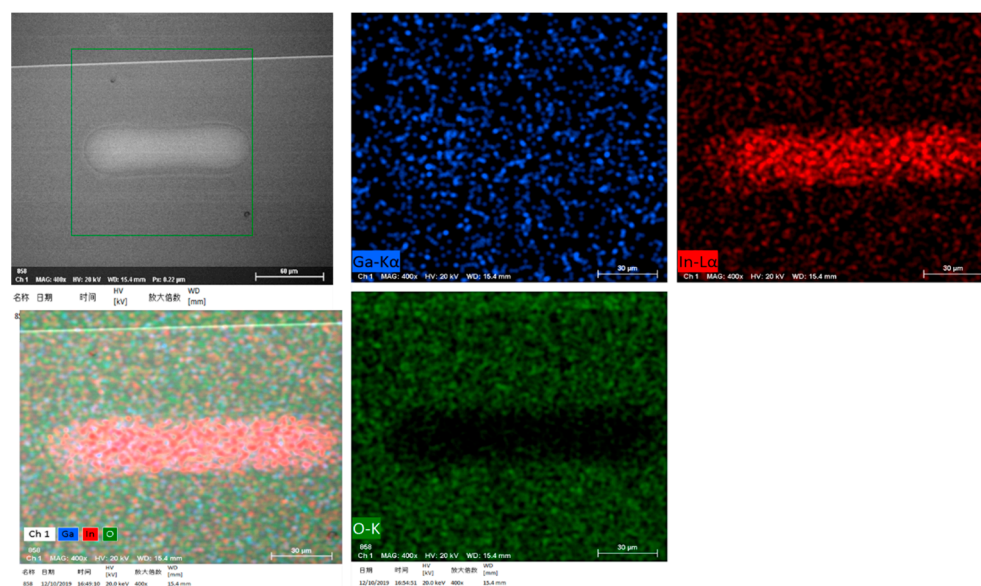
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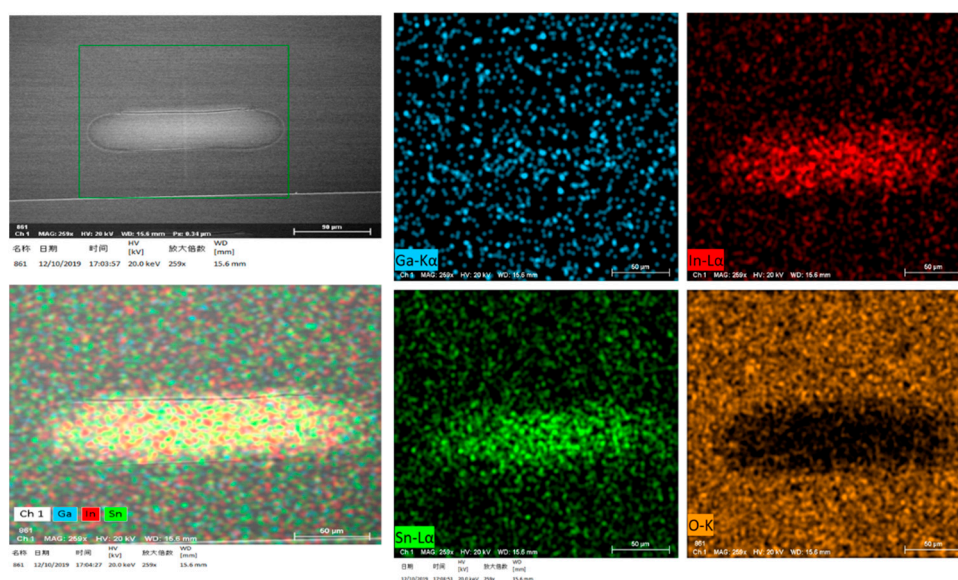
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**Figure S1:** The Daktak step profiling lines for (a) ITO S/D, (b) InGaSnO semiconductor, (c) AlO<sub>x</sub> insulator, and (d) ITO gate.



**Figure S2:** SEM image and the energy-dispersion x-ray spectroscopy (EDS) element distribution maps of the InGaO film.



**Figure S3:** SEM image and the EDS element distribution maps of the InGaSnO film.



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